

## Refine Search

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### Search Results -

Terms	Documents
L6 and DRAM	920

Database:

US Pre-Grant Publication Full-Text Database  
 US Patents Full-Text Database  
 US OCR Full-Text Database  
 EPO Abstracts Database  
 JPO Abstracts Database  
 Derwent World Patents Index  
 IBM Technical Disclosure Bulletins

Search:

L7






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### Search History

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DATE: Wednesday, February 15, 2006    [Printable Copy](#)    [Create Case](#)

#### Set Name Query

side by side

#### Hit Count Set Name

result set

*DB=USPT; PLUR=YES; OP=OR*

L7    L6 and DRAM    920    L7

L6    "embedded memory"    1974    L6

*DB=PGPB; PLUR=YES; OP=OR*

L5    "embedded memory"    1759    L5

L4    L3 and processor    1    L4

L3    L2 AND "28"    1    L3

L2    L1 AND "INSULATING REGION"    1    L2

L1    20060022302    1    L1

END OF SEARCH HISTORY

## Refine Search

### Search Results -

Terms	Documents
DRAM same (capacit\$5 near10 (dielectric) near7 (aluminum near5 oxide))	7

Database:

US Pre-Grant Publication Full-Text Database  
**US Patents Full-Text Database**  
 US OCR Full-Text Database  
 EPO Abstracts Database  
 JPO Abstracts Database  
 Derwent World Patents Index  
 IBM Technical Disclosure Bulletins

Search:

L19





### Search History

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<u>Set Name</u> side by side	<u>Query</u>	<u>Hit Count</u>	<u>Set Name</u> result set
	<i>DB=USPT; PLUR=YES; OP=OR</i>		
<u>L19</u>	DRAM same (capacit\$5 near10 (dielectric) near7 (aluminum near5 oxide))	7	<u>L19</u>
<u>L18</u>	DRAM same (capacit\$5 near6 (dielectric) near7 "metal-semiconductor")	0	<u>L18</u>
<u>L17</u>	Dram and (monocrystalline near4 ((electrode or plate) near3 capacitor))	9	<u>L17</u>
<u>L16</u>	Dram and (monocrystalline near6 ((electrode or plate) near3 capacitor))	22	<u>L16</u>
<u>L15</u>	Dram and (monocrystalline near10 ((electrode or plate) near5 capacitor))	35	<u>L15</u>
<u>L14</u>	Dram and (monocrystalline near10 capacitor)	88	<u>L14</u>
<u>L13</u>	Dram and (monocrystalline near10 capacitor)	0	<u>L13</u>
<u>L12</u>	L8 and monocrystal\$6	2	<u>L12</u>

*DB=PGPB; PLUR=YES; OP=OR*

<u>L11</u>	L1 and "auxiliary doping"	1	<u>L11</u>
<u>L10</u>	L1 and "auxiliary doping"	0	<u>L10</u>
<u>L9</u>	L1 and auxiliary	1	<u>L9</u>

*DB=USPT; PLUR=YES; OP=OR*

<u>L8</u>	DRAM and (tft same "storage capacitor" same substrate)	23	<u>L8</u>
<u>L7</u>	L6 and DRAM	920	<u>L7</u>
<u>L6</u>	"embedded memory"	1974	<u>L6</u>

*DB=PGPB; PLUR=YES; OP=OR*

<u>L5</u>	"embedded memory"	1759	<u>L5</u>
<u>L4</u>	L3 and processor	1	<u>L4</u>
<u>L3</u>	L2 AND "28"	1	<u>L3</u>
<u>L2</u>	L1 AND "INSULATING REGION"	1	<u>L2</u>
<u>L1</u>	20060022302	1	<u>L1</u>

END OF SEARCH HISTORY